

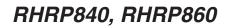
Is Now Part of



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### Data Sheet

## January 2002

## 8A, 400V - 600V Hyperfast Diodes

The RHRP840 and RHRP860 are hyperfast diodes with soft recovery characteristics ( $t_{rr} < 30$ ns). They have half the recovery time of ultrafast diodes and are silicon nitride passivated ion-implanted epitaxial planar construction.

These devices are intended for use as

freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Formerly developmental type TA49059.

## **Ordering Information**

PART NUMBER	PACKAGE	BRAND		
RHRP840	TO-220AC	RHRP840		
RHRP860	TO-220AC	RHRP860		

NOTE: When ordering, use the entire part number.

## Symbol



## Features

- Hyperfast with Soft Recovery......</br>

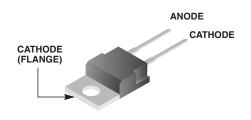
- Avalanche Energy Rated
- Planar Construction

## Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

## Packaging





#### **Absolute Maximum Ratings** $T_{C} = 25^{\circ}C$ , Unless Otherwise Specified

	RHRP840	RHRP860	UNITS
Peak Repetitive Reverse Voltage	400	600	V
Working Peak Reverse VoltageV <sub>RWM</sub>	400	600	V
DC Blocking Voltage	400	600	V
Average Rectified Forward Current	8	8	A
Repetitive Peak Surge CurrentI <sub>FRM</sub> (Square Wave, 20kHz)	16	16	А
Nonrepetitive Peak Surge Current I <sub>FSM</sub> (Halfwave, 1 Phase, 60Hz)	100	100	A
Maximum Power Dissipation	75	75	W
Avalanche Energy (See Figures 10 and 11)EAVL	20	20	mJ
Operating and Storage Temperature	-65 to 175	-65 to 175	oC

SYMBOL	TEST CONDITION	RHRP840			RHRP860			
		MIN	ТҮР	МАХ	MIN	ТҮР	MAX	UNITS
V <sub>F</sub>	I <sub>F</sub> = 8A	-	-	2.1	-	-	2.1	V
	I <sub>F</sub> = 8A, T <sub>C</sub> = 150 <sup>o</sup> C	-	-	1.7	-	-	1.7	V
I <sub>R</sub>	V <sub>R</sub> = 400V	-	-	100	-	-	-	μΑ
	V <sub>R</sub> = 600V	-	-	-	-	-	100	μA
	$V_{\rm R} = 400V, T_{\rm C} = 150^{\rm o}{\rm C}$	-	-	500	-	-	-	μA
	$V_{\rm R} = 600V, T_{\rm C} = 150^{\rm o}{\rm C}$	-	-	-	-	-	500	μΑ
t <sub>rr</sub>	$I_F = 1A$ , $dI_F/dt = 200A/\mu s$	-	-	30	-	-	30	ns
	$I_F = 8A$ , $dI_F/dt = 200A/\mu s$	-	-	35	-	-	35	ns
ta	$I_F = 8A$ , $dI_F/dt = 200A/\mu s$	-	18	-	-	18	-	ns
tb	$I_F = 8A$ , $dI_F/dt = 200A/\mu s$	-	10	-	-	10	-	ns
Q <sub>RR</sub>	$I_F = 8A$ , $dI_F/dt = 200A/\mu s$	-	56	-	-	56	-	nC
CJ	V <sub>R</sub> = 10V, I <sub>F</sub> = 0A	-	25	-	-	25	-	pF
$R_{\theta JC}$		-	-	2	-	-	2	°C/W

#### **Electrical Specifications** $T_{C} = 25^{\circ}C$ , Unless Otherwise Specified

DEFINITIONS

 $V_F$  = Instantaneous forward voltage (pw = 300µs, D = 2%).

I<sub>R</sub> = Instantaneous reverse current.

 $t_{rr}$  = Reverse recovery time (See Figure 9), summation of  $t_a + t_b$ .

 $t_a$  = Time to reach peak reverse current (See Figure 9).

 $t_b$  = Time from peak  $I_{RM}$  to projected zero crossing of  $I_{RM}$  based on a straight line from peak  $I_{RM}$  through 25% of  $I_{RM}$  (See Figure 9).

Q<sub>RR</sub> = Reverse recovery charge.

CJ = Junction capacitance.

 $R_{\theta JC}$  = Thermal resistance junction to case.

pw = Pulse width.

D = Duty cycle.

## **Typical Performance Curves**

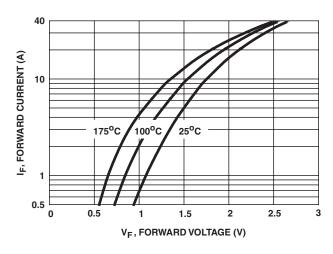


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

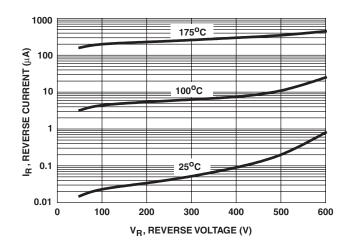


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

## Typical Performance Curves (Continued)

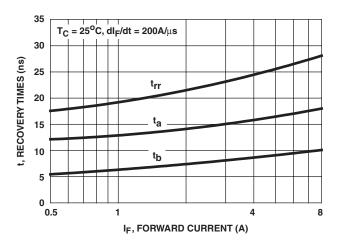
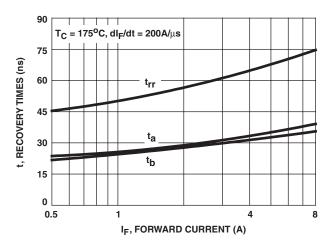


FIGURE 3. t<sub>rr</sub>, t<sub>a</sub> AND t<sub>b</sub> CURVES vs FORWARD CURRENT





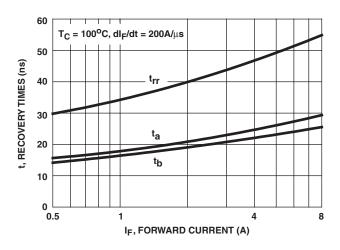


FIGURE 4.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

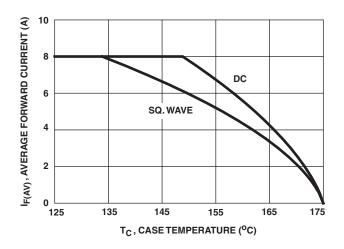


FIGURE 6. CURRENT DERATING CURVE

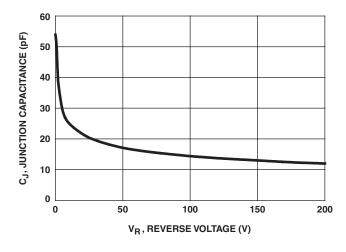
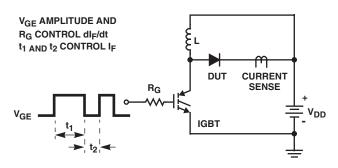


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

## **Test Circuits and Waveforms**





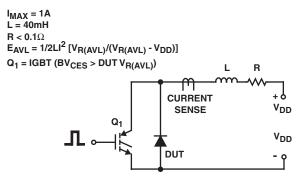


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

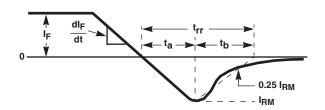


FIGURE 9. trr WAVEFORMS AND DEFINITIONS

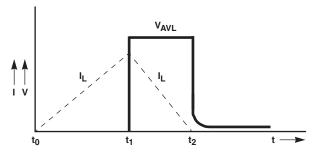


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

Ø 4.09 3.50 ⊕ 0.36 M B A M 10.67 В Α 9.65 8.89 3.43 1.40 6.86 2.54 0.51 6.86 **7**° 5.84 3° T 13.40 16.51 12,19 14,22 16.15 9.40 15,75 8.38 **5**° **5**° 3° 3° 6.35 MAX 2 1 0.60 MAX С 14.73 13,60 1.65 (1.91)1.25 F Т 0.61 2.54 0.33 1.02 2.92 0.38 2.03 5.08 ⊕ 0.36 M C A B **5° 5°** 3° 3° ..... -...... FAIRCHILD ... 4.80 4.30

#### NOTES:

- A. PACKAGE REFERENCE: JEDEC TO220,ISSUE K, VARIATION AC,DATED APRIL 2002.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DRAWING FILE NAME: TO220A02REV5

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